

FDD8451

N-Channel PowerTrench® MOSFET

40V, 28A, 24mΩ

Features

- Max $r_{DS(on)}$ = 24mΩ at $V_{GS} = 10V$, $I_D = 9A$
- Max $r_{DS(on)}$ = 30mΩ at $V_{GS} = 4.5V$, $I_D = 7A$
- Low gate charge
- Fast Switching
- High performance trench technology for extremely low $r_{DS(on)}$
- RoHS compliant

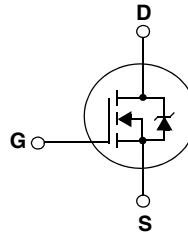
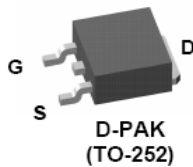


General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, fast switching speed and extremely low $r_{DS(on)}$.

Application

- DC/DC converter
- Backlight inverter



MOSFET Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	40	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current -Continuous @ $T_C=25^\circ\text{C}$	28	A
	-Continuous @ $T_A=25^\circ\text{C}$	9	
	-Pulsed (Note 1)	78	
E_{AS}	Single Pulse Avalanche Energy (Note 2)	20	mJ
P_D	Power Dissipation	37	W
T_J, T_{STG}	Operating and Storage Temperature	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	4.1	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	40	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	96	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD8451	FDD8451	D-PAK(TO-252)	13"	12mm	2500 units

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	40			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C		33.5		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 32\text{V}, V_{GS} = 0\text{V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	1	1.7	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$, referenced to 25°C		-5.7		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = 10\text{V}, I_D = 9\text{A}$		19	24	m Ω
		$V_{GS} = 4.5\text{V}, I_D = 7\text{A}$		23	30	
		$V_{GS} = 10\text{V}, I_D = 9\text{A}$ $T_J = 150^\circ\text{C}$		32	41	
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{V}, I_D = 9\text{A}$		29		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V},$ $f = 1\text{MHz}$		742	990	pF
C_{oss}	Output Capacitance			112	150	pF
C_{rss}	Reverse Transfer Capacitance			72	110	pF
R_g	Gate Resistance		$f = 1\text{MHz}$		1.1	

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 20\text{V}, I_D = 1\text{A}$ $V_{GS} = 10\text{V}, R_{GS} = 6\Omega$		7	14	ns
t_r	Rise Time			2	10	ns
$t_{d(off)}$	Turn-Off Delay Time			19	34	ns
t_f	Fall Time			5	10	ns
Q_g	Total Gate Charge at 10V	$V_{DS} = 20\text{V}, I_D = 9\text{A}$ $V_{GS} = 10\text{V}$		14	20	nC
Q_g	Total Gate Charge at 5V			7.7	11	nC
Q_{gs}	Gate to Source Gate Charge			2.3		nC
Q_{gd}	Gate to Drain "Miller" Charge			3.2		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 9\text{A}$		0.87	1.2	V
t_{rr}	Reverse Recovery Time	$I_F = 9\text{A}, di/dt = 100\text{A}/\mu\text{s}$		25	38	ns
Q_{rr}	Reverse Recovery Charge	$I_F = 9\text{A}, di/dt = 100\text{A}/\mu\text{s}$		19	29	nC

Notes:

- 1: Pulse time < 300 μs , Duty cycle = 2%.
- 2: Starting $T_J = 25^\circ\text{C}$, $L = 0.1\text{mH}$, $I_{AS} = 20\text{A}$, $V_{DD} = 36\text{V}$, $V_{GS} = 10\text{V}$.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

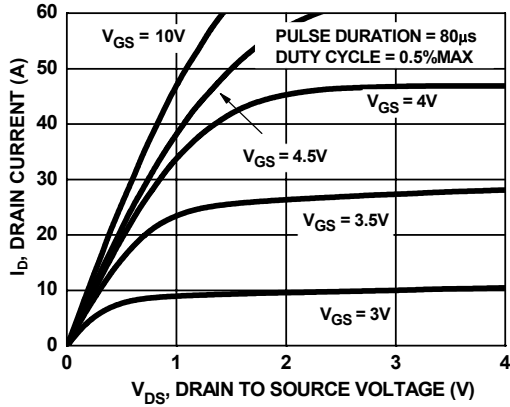


Figure 1. On Region Characteristics

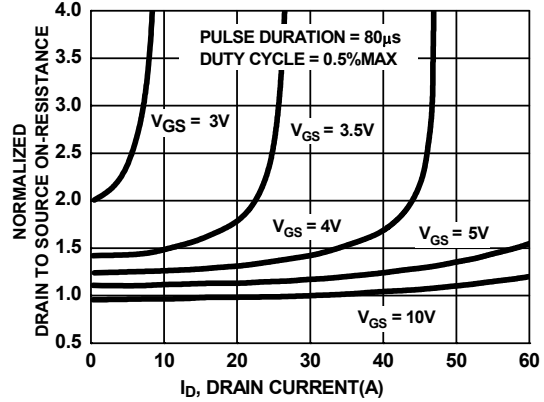


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

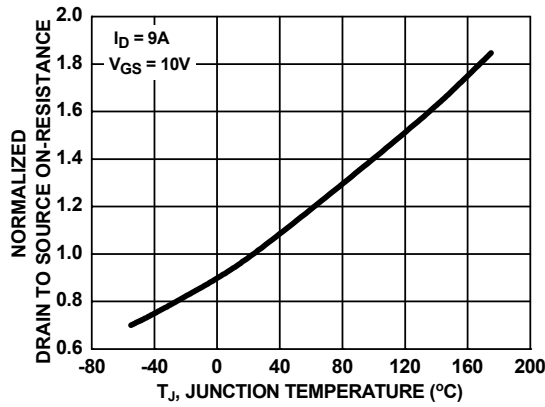


Figure 3. Normalized On Resistance vs Junction Temperature

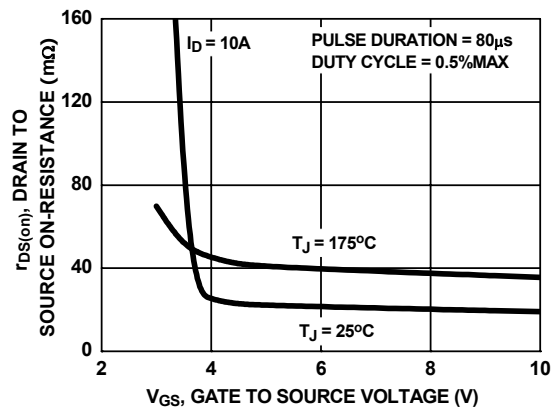


Figure 4. On-Resistance vs Gate to Source Voltage

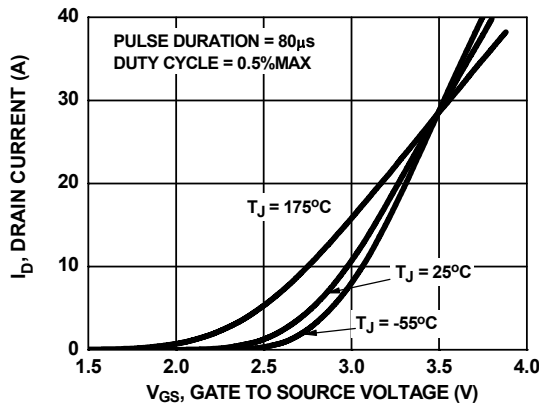


Figure 5. Transfer Characteristics

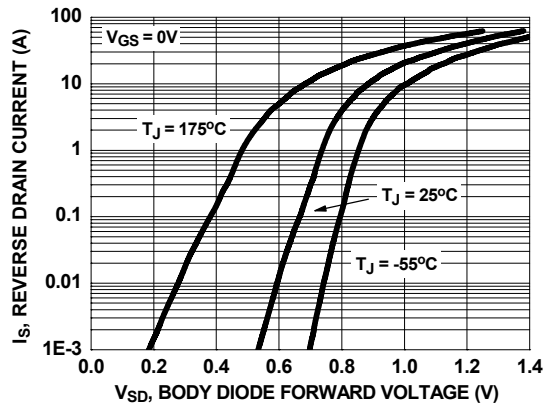


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

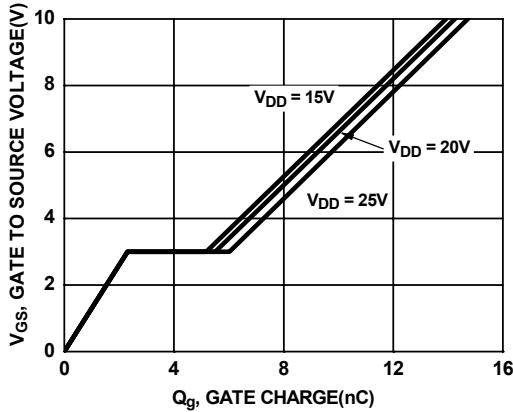


Figure 7. Gate Charge Characteristics

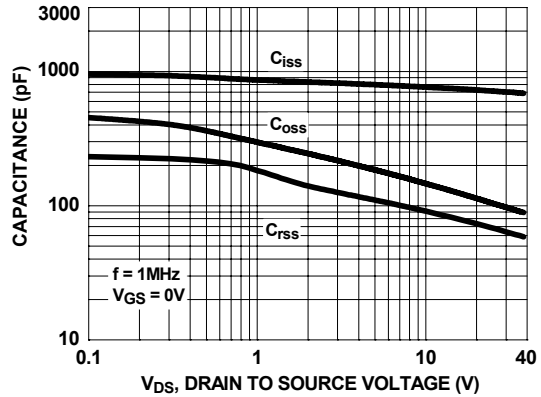


Figure 8. Capacitance vs Drain to Source Voltage

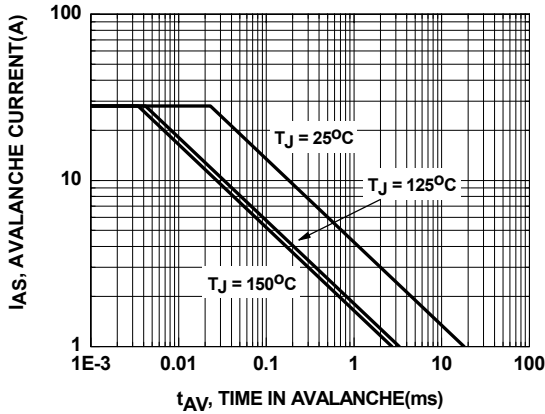


Figure 9. Unclamped Inductive Switching Capability

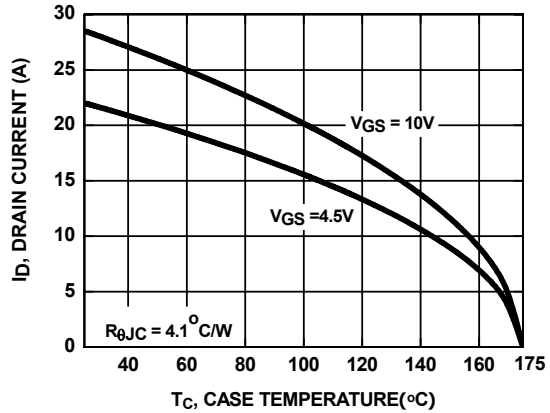


Figure 10. Maximum Continuous Drain Current vs Case Temperature

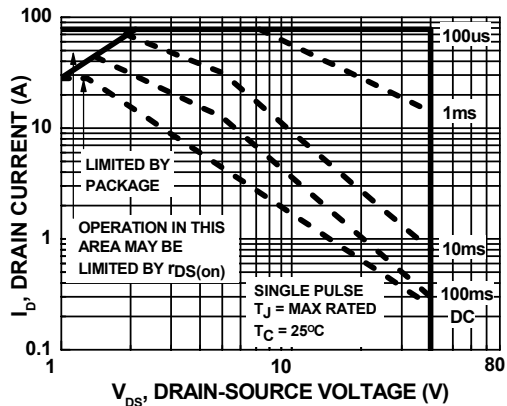


Figure 11. Forward Bias Safe Operating Area

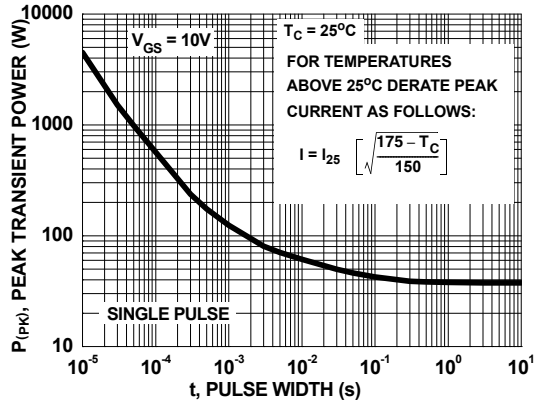
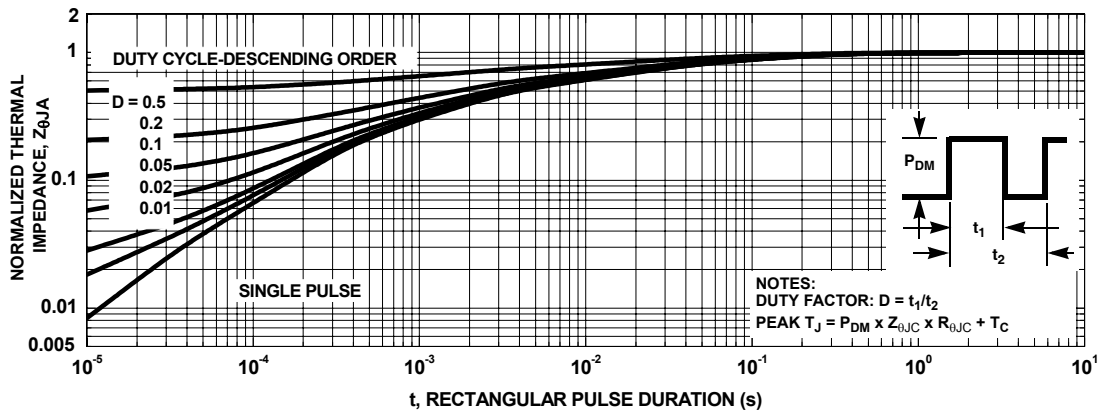


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted



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CROSSVOLT™	GTO™	MICROWIRE™	QT Optoelectronics™	TCM™
DOMET™	HiSeC™	MSX™	Quiet Series™	TinyLogic®
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